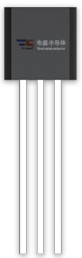
2N5400 TRANSISTOR (PNP)



TO-92

1.EMITTER
2.COLLECTOR
3.BASE

FEATURE

- **Switching and Amplification in High Voltage Applications such as Telephony**
- **Low Current(max. 600mA)**
- **High Voltage(max.130v)**

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2N5400	TO-92	Bulk	1000pcs/Bag
2N5400-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-130	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.6	A
P_D	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	℃ /W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-130			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -10μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -100 V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -3 V, I_C=0			-0.1	μA
DC current gain	h_{FE1}	V_{CE}= -5 V, I_C=-1mA	30			
	h_{FE2}	V_{CE}= -5 V, I_C= -10mA	40		180	
	h_{FE3}	V_{CE}= -5 V, I_C=-50mA	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -10mA, I_B= -1mA			-0.2	V
	$V_{CE(sat)}$	I_C= -50mA, I_B= -5mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= -10mA, I_B= -1mA			-1	V
	$V_{BE(sat)}$	I_C= -50mA, I_B= -5mA			-1	V
Transition frequency	f_T	V_{CE}=-10V, I_C=-10mA f =30MHz	100			MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz			6	pF